

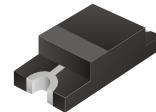
SMD Schottky Barrier Diode

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CDBN0245

I_o = 200 mA

V_R = 45 Volts



Features

Designed for mounting on small surface

Extremely thin package

Low stored charge

Majority carrier conduction

Mechanical data

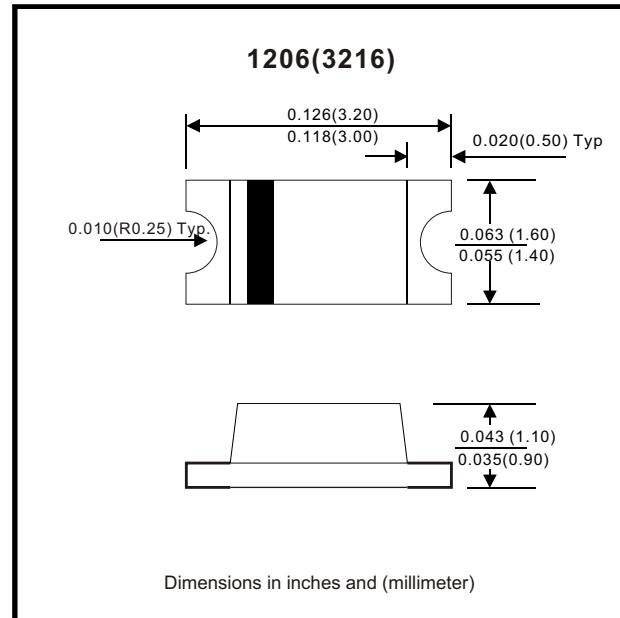
Case: 1206(3216) Standard package,
molded plastic .

Terminals: Solder plated, solderable per
MIL-STD-750, method 2026.

Polarity: Indicated by cathode band.

Mounting position: Any.

Weight: 0.0085 gram. (approximately)



Maximum Rating (at T_A = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		V _{RRM}			50	V
Reverse voltage		V _R			45	V
Average forward current		I _o			200	mA
Forward current , surge peak	8.3 ms single half sine-wave superimposed on rate load(JEDEC method)	I _{FSM}		3000		m A
Power Dissipation		P _D			250	mW
Storage temperature		T _{TG}	-40		+125	°C
Junction temperature		T _j	-40		+125	°C

Electrical Characteristics (at T_A = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 200 mADC	V _F			0.55	V
Reverse current	V _R = 45 V	I _R			30	uA
Capacitance between terminals	f = 1MHz, and 10 VDC reverse voltage	C _T		10		pF

RATING AND CHARACTERISTIC CURVES (CDBN0245)

Fig. 1 - Forward characteristics

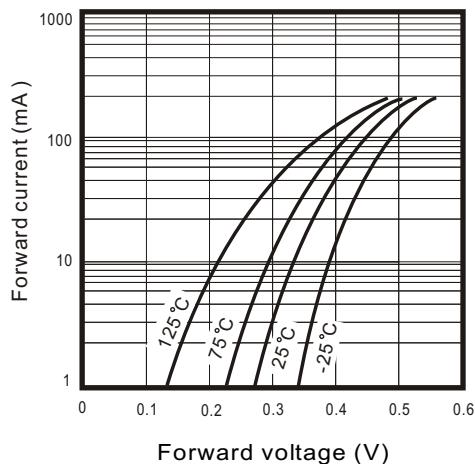


Fig. 2 - Reverse characteristics

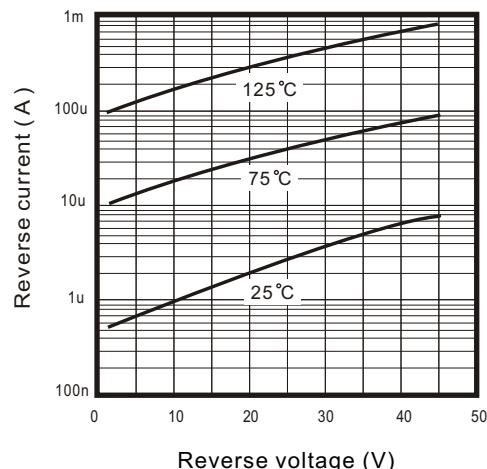


Fig. 3 - Capacitance between terminals characteristics

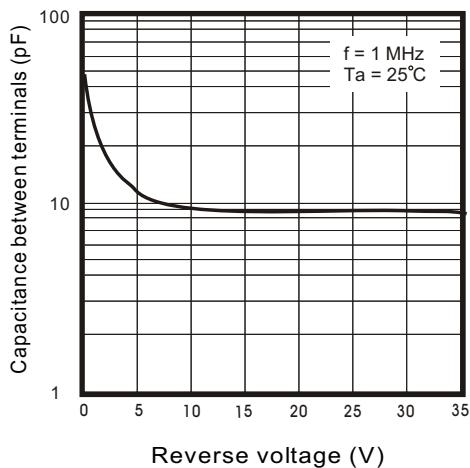


Fig. 4 - Current derating curve

